

XN04130 (XN4130)

Silicon PNP epitaxial planar type

For amplification of low-frequency output

■ Features

- Two elements incorporated into one package
(Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- UNR1130 (UN1130) × 2

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-15	V
Collector-emitter voltage (Base open)	V_{CEO}	-15	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_{C}	-0.5	A
Peak collector current	I_{CP}	-1	A
Total power dissipation	P_{T}	300	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

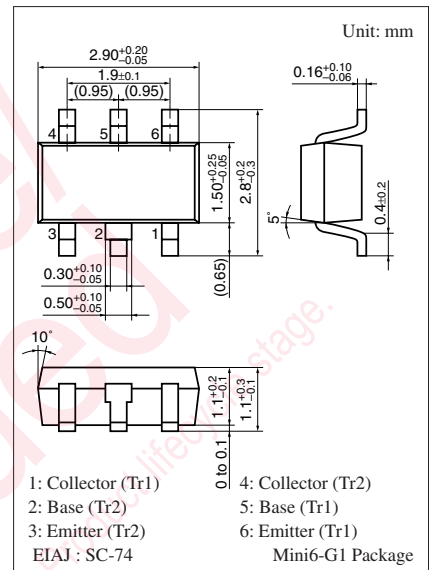
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}$, $I_{\text{E}} = 0$	-15			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -1 \text{ mA}$, $I_{\text{B}} = 0$	-15			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\text{E}} = -1 \text{ mA}$, $I_{\text{C}} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -10 \text{ V}$, $I_{\text{E}} = 0$			-0.1	μA
Forward current transfer ratio *	h_{FE1}	$V_{\text{CE}} = -2 \text{ V}$, $I_{\text{C}} = -500 \text{ mA}$	80		280	—
	h_{FE2}	$V_{\text{CE}} = -2 \text{ V}$, $I_{\text{C}} = -1 \text{ A}$	50			
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -300 \text{ mA}$, $I_{\text{B}} = -6 \text{ mA}$		-0.2	-0.3	V
Base-emitter saturation voltage	$V_{\text{BE(sat)}}$	$I_{\text{C}} = -300 \text{ mA}$, $I_{\text{B}} = -6 \text{ mA}$		-0.9	-1.3	V
Transition frequency	f_{T}	$V_{\text{CB}} = -10 \text{ V}$, $I_{\text{E}} = 50 \text{ mA}$, $f = 200 \text{ MHz}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{\text{CB}} = -10 \text{ V}$, $I_{\text{E}} = 0$, $f = 1 \text{ MHz}$		22		pF
Base-emitter resistance	R_{BE}		-30%	10	+30%	k Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

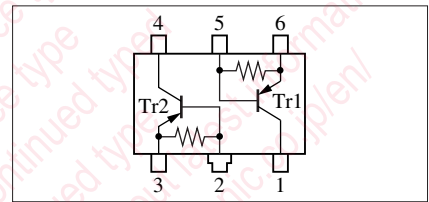
2. *: Pulse measurement

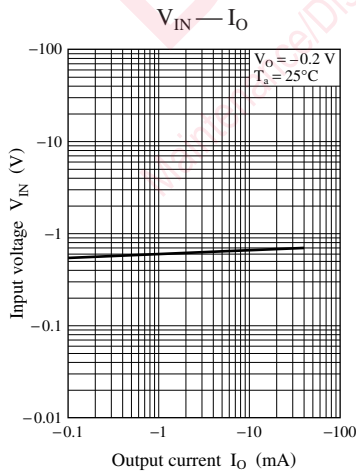
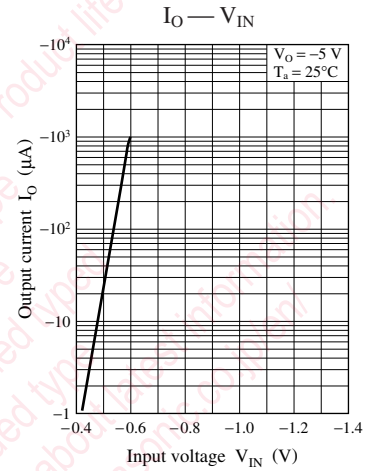
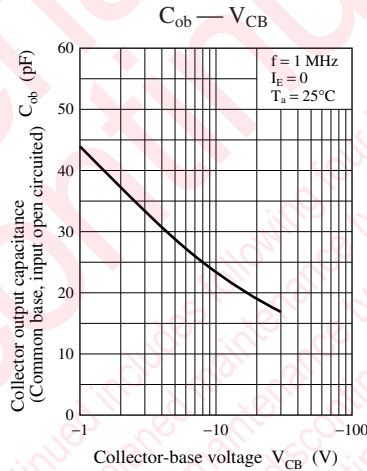
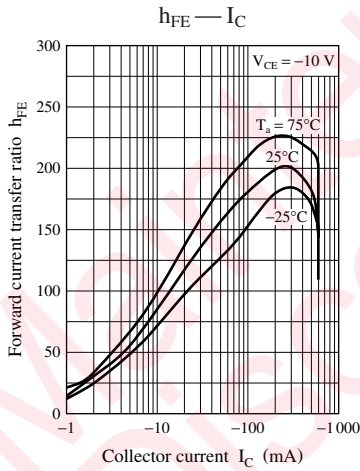
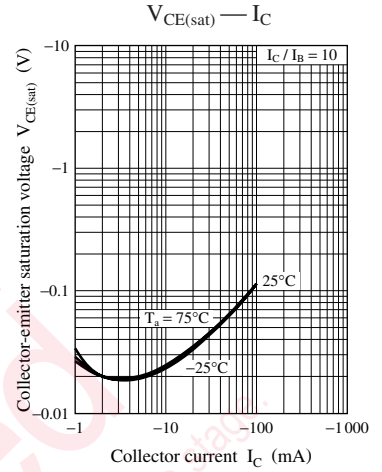
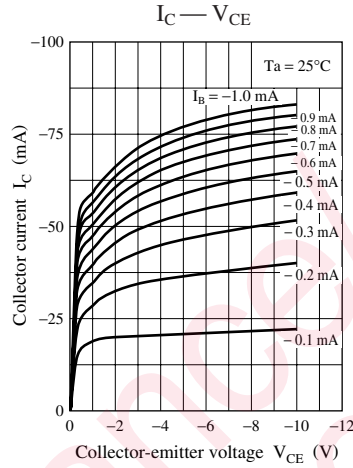
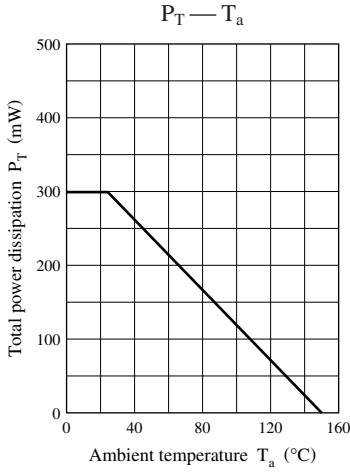
Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: OF

Internal Connection





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